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The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Cancelled)

2. (Currently Amended) A method for processing a work piece with a plasma forming component of a process recipe, comprising:

providing a process chamber within which the work piece is processed, and which includes at least a first processing zone and a second processing zone, each zone representing a portion of the work piece to be processed;

outputting the plasma forming component into the first processing zone of the process chamber without outputting the plasma forming component into the second processing zone of the process chamber, the plasma forming component being outputted into the first processing zone from a peripheral location of the process chamber;

outputting the plasma forming component into the second processing zone of the process chamber without outputting the plasma forming component into the first processing zone of the process chamber, the plasma forming component being outputted into the second processing zone from a peripheral location of the process chamber; and

continuously switching between the step of outputting the plasma forming component into the first processing zone and the step of outputting the plasma forming component into the second processing zone so as to effect the concentration of the plasma forming component between the first and second processing zones while continuously generating or sustaining a single plasma within the first and second processing zones inside the process chamber.

3. (Previously Presented) The method as recited in claim 2 further including varying the magnitude of the plasma forming component between each of the processing zones such that the magnitude of the plasma forming component at the first processing zone is different than the magnitude of the plasma forming component at the second processing zone.

4. (Previously Presented) The method as recited in claim 2 further including setting the timing of the switching step such that the outputting time at the first processing zone is different than the outputting time at the second processing zone.

5. (Previously Presented) The method as recited in claim 2 further including varying the constituents of the plasma forming component between each of the processing zones such that the constituents of the plasma forming component at the first processing zone is different than the constituents of the plasma forming component at the second processing zone.

6. (Previously Presented) The method as recited in claim 2 further including varying the ratio of constituents of the plasma forming component between each of the processing zones such that the ratio at the first processing zone is different than the ratio of the plasma forming component at the second processing zone.

7. (Previously Presented) The method as recited in claim 2 further including,

varying the magnitude of the plasma forming component between each of the processing zones such that the magnitude of the plasma forming component at the first processing zone is different than the magnitude of the plasma forming component at the second processing zone;

varying setting the timing of the switching step such that the outputting time at the first processing zone is different than the outputting time at the second processing zone;

varying the constituents of the plasma forming component between each of the processing zones such that the constituents of the plasma forming component at the first processing zone is different than the constituents of the plasma forming component at the second processing zone; and

varying the ratio of constituents of the plasma forming component between each of the processing zones such that the ratio at the first processing zone is different than the ratio of the plasma forming component at the second processing zone.

8. (Original) The method as recited in claim 2 wherein the first processing zone corresponds to a center portion of the work piece and the second processing zone corresponds to an outer portion of the work piece.

9. (Previously Presented) The method as recited in claim 2 further including supplying the plasma forming component from a single component source.

10. (Cancelled)

11. (Currently Amended) The method as recited in claim 2 wherein the plasma forming component is energy for igniting or sustaining the plasma.

12. (Previously Presented) The method as recited in claim 11 wherein the steps of outputting the plasma forming component includes producing an electric field inside the process chamber.

13. (Previously Presented) The method as recited in claim 2 wherein the plasma forming component is gas.

14. (Previously Presented) The method as recited in claim 2 wherein the steps of outputting the plasma forming component includes releasing a gaseous source material inside the process chamber.

15. (Currently Amended) A method of forming a plasma inside a process chamber, comprising:

continuously receiving a plasma forming component from a single component source;

alternately distributing the received plasma forming component between two different regions of the process chamber so as to effect the concentration of the plasma forming component in the different regions of the process chamber [[while]], the plasma forming component that is alternately distributed to the two different regions helping continuously form ~~generating or sustaining~~ a plasma ~~continuously~~ within the process chamber during a single processing event associated with a work piece.

16. (Original) The method as recited in claim 15 wherein the different regions include an inner region and an outer region.

17. (Original) The method as recited in claim 15 wherein the plasma forming component is gas.

18. (Currently Amended) The method as recited in claim 15 wherein the plasma forming component is energy for igniting or sustaining the plasma.

19. (Previously Presented) The method as recited in claim 15 further including,

receiving a second plasma forming component from a second single component source, the second plasma forming component being different than the first plasma forming component; and

alternately distributing the received second plasma forming component between two different regions of the process chamber so as to effect the concentration of the second plasma forming component in the different regions of the process chamber while generating or sustaining a plasma continuously within the process chamber.

20. (Currently Amended) The method as recited in claim 19 wherein the first plasma forming component is gas and the second plasma forming component is energy for igniting or sustaining the plasma.

21. (Currently Amended) A method for processing a semiconductor substrate, said method comprising:

continuously delivering plasma forming components to a process chamber in order to continuously form a plasma for processing a center and edge of a top surface of the semiconductor substrate at the same time, the process chamber including an empty space for forming the plasma that is at least defined by a top surface and side surface of the process chamber;

via time multiplexing, selectively switching the delivery of the plasma forming components back and forth between a first delivery condition where the plasma forming components are only delivered to an inner region of the process chamber[,] and a second delivery condition where the plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the plasma forming component [in] between [an] the inner and [an] the outer region of the process chamber, the first delivery condition allowing the plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same plasma forming components from being delivered into the inner region of the process chamber.

wherein the plasma forming components are peripherally outputted into the process chamber,

wherein the inner region of the process chamber is associated with the center of the semiconductor substrate and the outer region of the process chamber is associated with the edge of the semiconductor substrate

22. (Previously Presented) The method as recited in claim 12 wherein the electric field is inductively coupled into the process chamber via an external electrode disposed outside the process chamber.

23. (Previously Presented) The method as recited in claim 19 wherein the distribution of the received first component and the received second component is controlled separately.

24. (Previously Presented) The method as recited in claim 23 wherein the distribution of the received first component and the received second component follow different time scales.

25. (Cancelled)

26. (Previously Presented) The method as recited in claim 21 wherein the plasma forming component is gas.

27. (Previously Presented) The method as recited in claim 21 wherein the plasma forming component is energy.

28. (Currently Amended) ~~The method as recited in claim 21 further including,~~ A method for processing a semiconductor substrate, said method comprising:

continuously delivering plasma forming components to a process chamber;

via time multiplexing, selectively switching the delivery of the plasma forming components back and forth between a first delivery condition where the plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the plasma forming components to be delivered into an inner region of a process

chamber while at the same time preventing the same plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same plasma forming components from being delivered into the inner region of the process chamber;

continuously delivering second plasma forming components to the process chamber;

via a second time multiplexing operation that is separate from the time multiplexing operation associated with the plasma forming components, selectively switching the delivery of the second plasma forming components back and forth between a first delivery condition where the second plasma forming components are only delivered to an inner region of the process chamber, and a second delivery condition where the second plasma forming components are only delivered to an outer region of the process chamber so as to effect the concentration of the second plasma forming component in an inner and an outer region of the process chamber, the first delivery condition allowing the second plasma forming components to be delivered into an inner region of a process chamber while at the same time preventing the same second plasma forming components from being delivered into an outer region of the process chamber, the second delivery condition allowing the second plasma forming components to be delivered into the outer region of the process chamber while at the same time preventing the same second plasma forming components from being delivered into the inner region of the process chamber,

wherein the plasma forming components correspond[ing] to energy, and the second plasma forming components correspond[ing] to gas.

29. (Currently Amended) The method as recited in claim 21 wherein the plasma forming component is outputted the same distance from the work piece when outputted to the first processing zone and the second processing zone.

30. (New) A method of forming a plasma associated with etching a semiconductor substrate, said method comprising:

continuously supplying power from a single power source;

continuously supplying a flow of gas from a single gas source while the power is being supplied;

via time multiplexing, alternately producing first and second electric fields inside the process chamber with the supplied power, the first electric field being produced at a first

region of a processing zone, the second electric field being produced at a second region of the processing zone, the first and second electric fields being produced according to a power time sequence that is divided into a plurality of time slices;

controlling the parameters associated with the first and second electric fields at each time slice in order to effect the amount of ions in the first and second regions of the processing zone;

via time multiplexing, alternately releasing the supplied gas into the process chamber at a first region and a second region of the processing zone, the gases being released according to a gas time sequence that is divided into a plurality of time slices;

controlling the parameters associated with the released gas at each time slice in order to effect the amount of neutrals in the first and second regions of the processing zone.

31. (New) The method as recited in claim 30 wherein the gas time sequence and power time sequence follow the same time scale.

32. (New) The method as recited in claim 30 wherein the gas time sequence and power time sequence follow different time scales.

33. (New) The method as recited in claim 30 wherein the amount of power used to create the first and second electric fields is different or wherein the time slices used to create the first and second electric fields are different in order to effect the amount of ions in the first and second regions of the processing zone.

34. (New) The method as recited in claim 30 wherein the flow rates delivered to the first region and the second region are different or wherein the time slices associated with releasing gas to the first region are different than the time slices associated with releasing gas to the second region in order to effect the amount of neutrals in the first and second regions of the processing zone.

35. (New) The method as recited in claim 30 wherein the parameters associated with the first and second electric fields are controlled so that the amount of ions in the outer region are different than the amount of ions in the inner region in order to improve processing uniformity.

36. (New) The method as recited in claim 30 wherein the parameters associated with the released gas are controlled so that the amount of neutrals in the outer region are different than the amount of neutrals in the inner region in order to improve processing uniformity.

37. (New) The method as recited in claim 30 wherein the electric fields are inductively coupled into the process chamber.

38. (New) The method as recited in claim 30 wherein the first and second regions correspond to an inner region and an outer region, and wherein the inner region is associated with a center portion of the substrate and the outer region is associated with an edge portion of the substrate.